

**NTE375**  
**Silicon NPN Transistor**  
**TV Vertical Output**  
**(Compl to NTE398)**

**Absolute Maximum Ratings:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Collector–Base Voltage, $V_{CBO}$ .....	200V
Collector–Emitter Voltage, $V_{CEO}$ .....	150V
Emitter–Base Voltage, $V_{EBO}$ .....	6V
Collector Current, $I_C$	
Continuous .....	2A
Peak .....	10A
Collector Dissipation ( $T_A = +25^\circ\text{C}$ ), $P_C$ .....	1.75W
Collector Dissipation ( $T_C = +25^\circ\text{C}$ ), $P_C$ .....	25W
Operating Junction Temperature, $T_J$ .....	+150°C
Storage Temperature Range, $T_{stg}$ .....	-40° to +150°C

**Electrical Characteristics:** ( $T_A = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 180\text{V}, I_E = 0$	–	–	1.0	mA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB} = 5\text{V}, I_C = 0$	–	–	5.0	mA
DC Current Gain	$h_{FE}$	$V_{CE} = 2\text{V}, I_C = 500\text{mA}$	100	–	200	
Gain Bandwidth Product	$f_T$	$V_{CE} = 5\text{V}, I_C = 500\text{mA}$	–	8	–	MHz
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 1\text{A}, I_B = 100\text{mA}$	–	–	1.5	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 1\text{A}, I_B = 100\text{mA}$	–	–	1.8	V

